# 2SJ0674

# Silicon P-channel MOS FET

#### For switching circuits

#### ■ Features

- Low ON resistance Ron
- High-speed switching
- SSSMini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

# ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V <sub>DSS</sub>	-30	V	
Gate-source surrender voltage	V <sub>GSS</sub>	±12	V	
Drain current	$I_D$	-100	mA	
Peak drain current	$I_{DP}$	-200	mA	
Power dissipation	$P_{\mathrm{D}}$	100	mW	
Channel temperature	T <sub>ch</sub>	125	°C	
Storage temperature	T <sub>stg</sub>	-55 to +125	°C	

### ■ Package

Code

SSSMini3-F1

- Pin Name
  - 1: Gate
  - 2: Source
  - 3: Drain

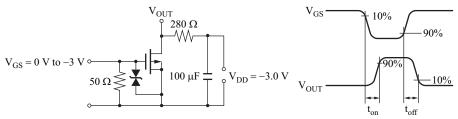
### ■ Marking Symbol: 5U

# ■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	$I_D = -10 \mu\text{A},  V_{GS} = 0$	-30			V
Drain-source cutoff current	$I_{\mathrm{DSS}}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0$			-1.0	μΑ
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$			±10	μΑ
Gate threshold voltage	$V_{TH}$	$I_D = -1.0 \mu A, V_{DS} = -3.0 V$	-0.5	-1.0	-1.5	V
Drain-source ON resistance	D	$I_D = -10 \text{ mA}, V_{GS} = -2.5 \text{ V}$		13	30	Ω
	R <sub>DS(on)</sub>	$I_D = -10 \text{ mA}, V_{GS} = -4.0 \text{ V}$		9	18	
Forward transfer admittance	Y <sub>fs</sub>	$I_D = -10 \text{ mA}, V_{DS} = -3 \text{ V}, f = 1 \text{ kHz}$	20	40		mS
Short-circuit input capacitance (Common source)	C <sub>iss</sub>	$V_{DS} = -3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		12		pF
Short-circuit output capacitance (Common source)	C <sub>oss</sub>			13		pF
Reverse transfer capacitance (Common source)	C <sub>rss</sub>			7		pF
Turn-on time *	t <sub>on</sub>	$V_{DD} = -3 \text{ V}, V_{GS} = 0 \text{ V to } -3 \text{ V}, I_D = -10 \text{ mA}$		300		ns
Turn-off time *	t <sub>off</sub>	$V_{DD} = -3 \text{ V}, V_{GS} = -3 \text{ V to } 0 \text{ V}, I_D = -10 \text{ mA}$		400		ns

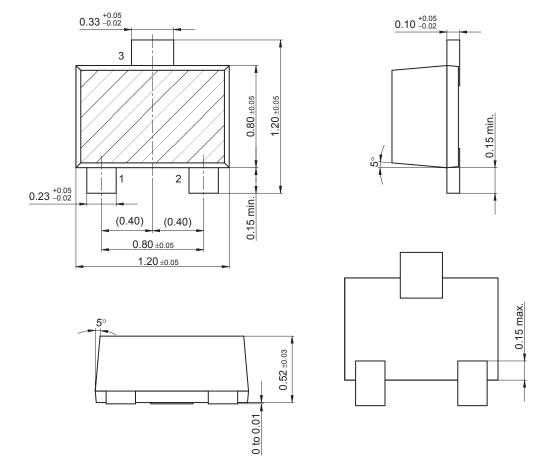
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*:  $t_{on}$ ,  $t_{off}$  measurement circuit



SSSMini3-F1

Unit: mm



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